



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	40V
I_D	310A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	0.95m
100% EAS Tested	
100% V_{DS} Tested	

General Description

Excellent package for heat dissipation

YJG310G04HJRQ

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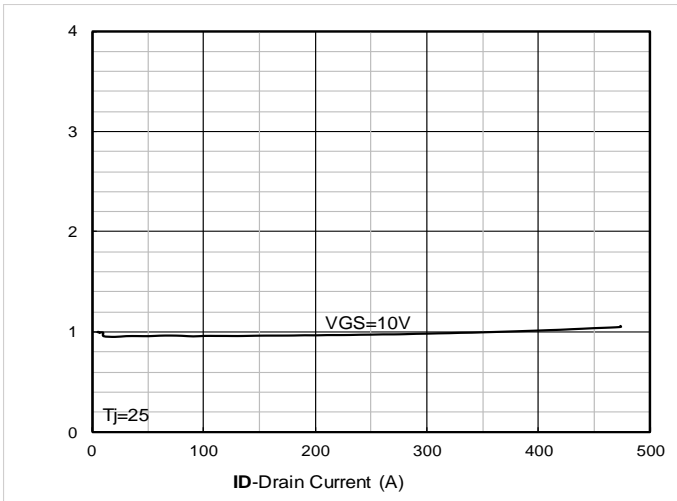


Figure 7. RDS(on) VS Drain Current

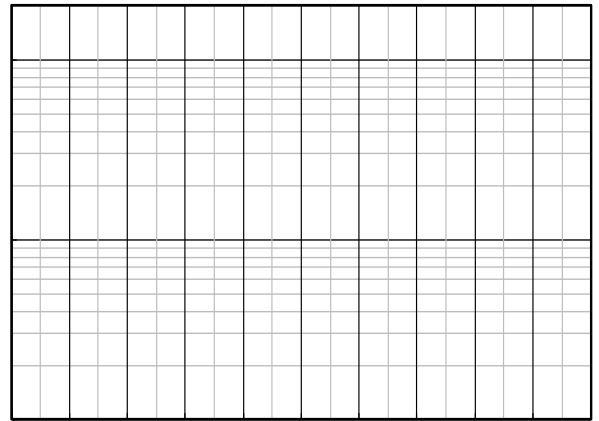


Figure 8. Forward characteristics of reverse diode

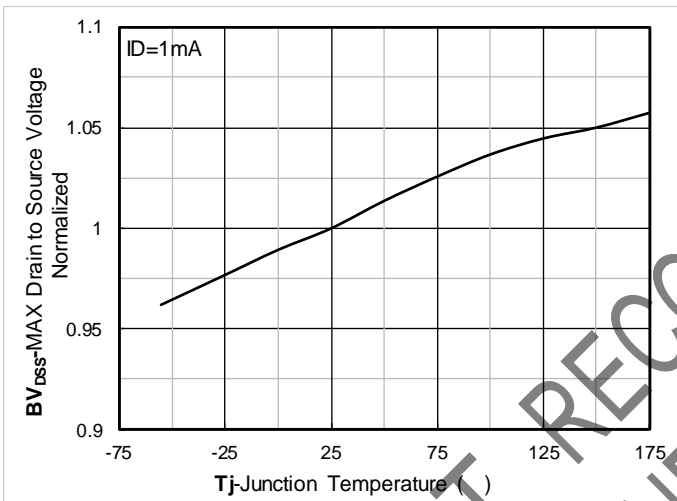


Figure 9. Normalized breakdown voltage

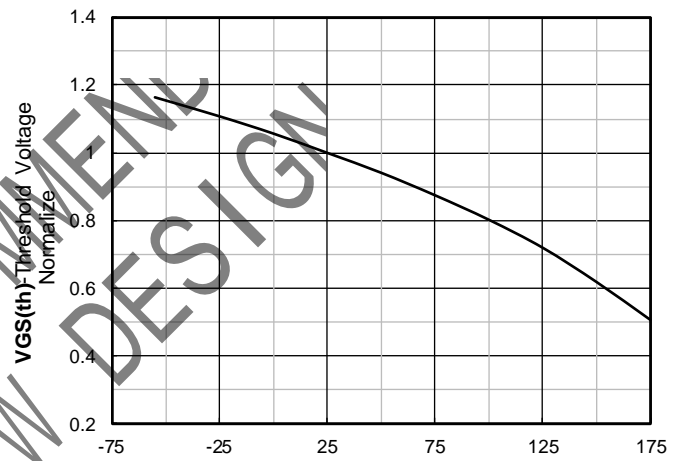


Figure 10. Normalized Threshold voltage

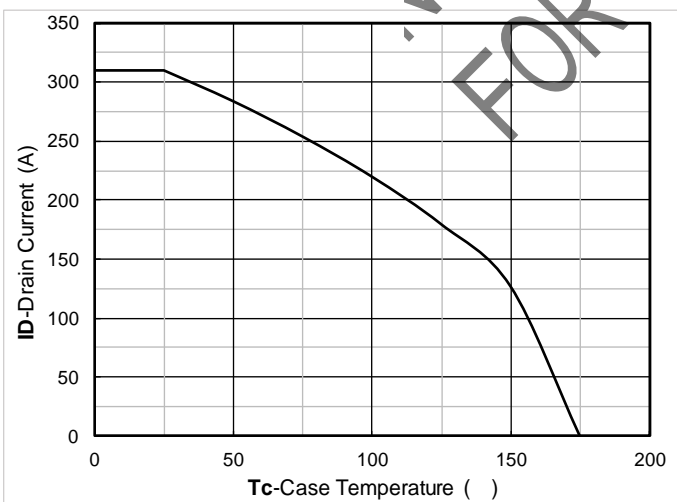


Figure 11. Current dissipation

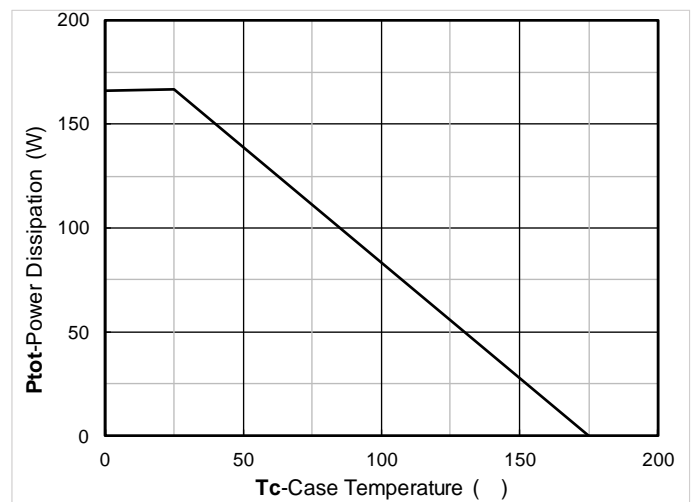


Figure 12. Power dissipation

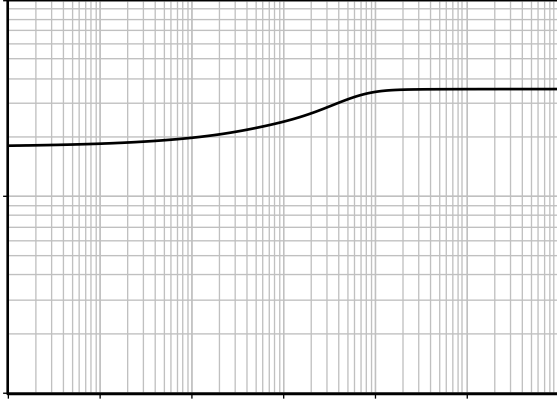


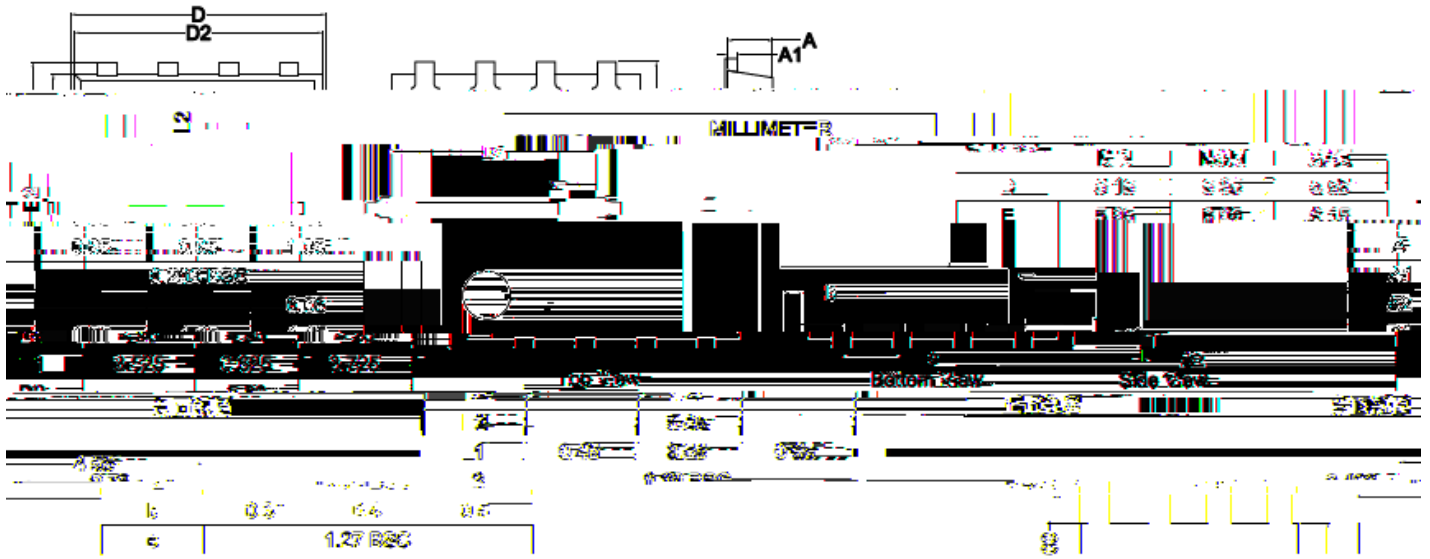
Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area

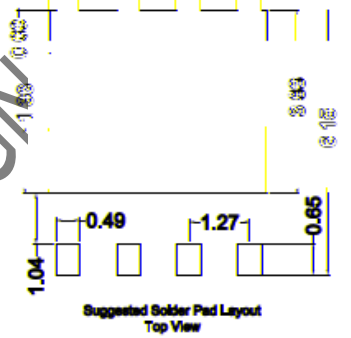
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PDFN5060-8L-0.95MM Package information



Notes:
1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.10 mm.
3. The pad layout is for reference purposes only.



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Disclaimer

The information presented in this document is for reference only. It is not intended to be used as a design or manufacturing specification. The user is responsible for verifying the information and ensuring that the product meets their requirements. The information is subject to change without notice.